

Masanori Nagase

List of Publications by Year in descending order

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papers

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1051969

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#	ARTICLE	IF	CITATIONS
1	Growth and Characterization of GaN/AlN Resonant Tunneling Diodes for High-Performance Nonvolatile Memory. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2000495.	0.8	1
2	Switching characteristics of nonvolatile memory using GaN/AlN resonant tunneling diodes. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 091001.	0.8	3
3	Stabilization of nonvolatile memory operations using GaN/AlN resonant tunneling diodes by reducing structural inhomogeneity. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 070310.	0.8	6
4	Resistance switching memory operation using the bistability in current-voltage characteristics of GaN/AlN resonant tunneling diodes. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 100301.	0.8	9
5	Investigating the bistability characteristics of GaN/AlN resonant tunneling diodes for ultrafast nonvolatile memory. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 034201.	0.8	14
6	Bistability Characteristics of GaN/AlN Resonant Tunneling Diodes Caused by Intersubband Transition and Electron Accumulation in Quantum Well. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 1321-1326.	1.6	22
7	Vertical Diamond Schottky Barrier Diode Fabricated on Insulating Diamond Substrate Using Deep Etching Technique. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 1416-1420.	1.6	14
8	Selective-Area Growth of Thick Diamond Films Using Chemically Stable Masks of Ru/Au and Mo/Au. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 070202.	0.8	2
9	High temperature application of diamond power device. <i>Diamond and Related Materials</i> , 2012, 24, 201-205.	1.8	133
10	Ultrafast All-Optical Gating Operation Using Michelson Interferometer for Hybrid Integration of Intersubband Transition Switch on Si Platform. <i>IEEE Photonics Technology Letters</i> , 2011, 23, 1884-1886.	1.3	4
11	All-Optical Demultiplexing from 160 to 40/80 Gb/s Using Mach-Zehnder Switches Based on Intersubband Transition of InGaAs/AlAsSb Coupled Double Quantum Wells. <i>IEICE Transactions on Electronics</i> , 2009, E92-C, 187-193.	0.3	11
12	Enhancement of All-Optical Cross Phase Modulation in InGaAs/AlAsSb Coupled Quantum Wells Using InAlAs Coupling Barriers. <i>IEEE Photonics Technology Letters</i> , 2008, 20, 2183-2185.	1.3	11
13	Mechanism of ultrafast modulation of the refraction index in photoexcited $\ln \left(\frac{1 + \frac{25}{\mu}}{1 + \frac{25}{\mu}} \right)$ <i>Physical Review B</i> , 2008, 78, . . .	1.1	25
14	All-optical demultiplexing of 160-Gbit/s signals with Mach-Zehnder interferometric switch utilizing intersubband transition in InGaAs/AlAsSb quantum well. <i>Applied Physics Letters</i> , 2007, 91, 221115.	1.5	62
15	Ultrafast All-Optical Refractive Index Modulation in Intersubband Transition Switch Using InGaAs/AlAs/AlAsSb Quantum Well. <i>Japanese Journal of Applied Physics</i> , 2007, 46, L157-L160.	0.8	24
16	Cross-phase-modulation-based wavelength conversion using intersubband transition in InGaAs/AlAs/AlAsSb coupled quantum wells. <i>Optics Letters</i> , 2007, 32, 751.	1.7	68
17	Intersubband transitions in InGaAs/AlAsSb coupled double quantum wells with InAlAs coupling barriers. , 2007, , .		0
18	Photorefectance study of InGaAs/AlAsSb quantum wells grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2007, 301-302, 177-180.	0.7	5

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19	Strain compensation for InGaAs/AlAs/AlAsSb coupled double quantum wells by controlling the barrier layer composition. Journal of Crystal Growth, 2007, 301-302, 240-243.	0.7	5
20	Phase-Breaking Effect Appearing in the Current-Voltage Characteristics of Double-Barrier Resonant Tunneling Diodes -Theoretical Fitting Over Four Orders of Magnitude-. Japanese Journal of Applied Physics, 2001, 40, 3018-3022.	0.8	6
21	Diamond Vertical Schottky Barrier Diode with Al ₂ O ₃ Field Plate. Materials Science Forum, 0, 717-720, 1319-1321.	0.3	10